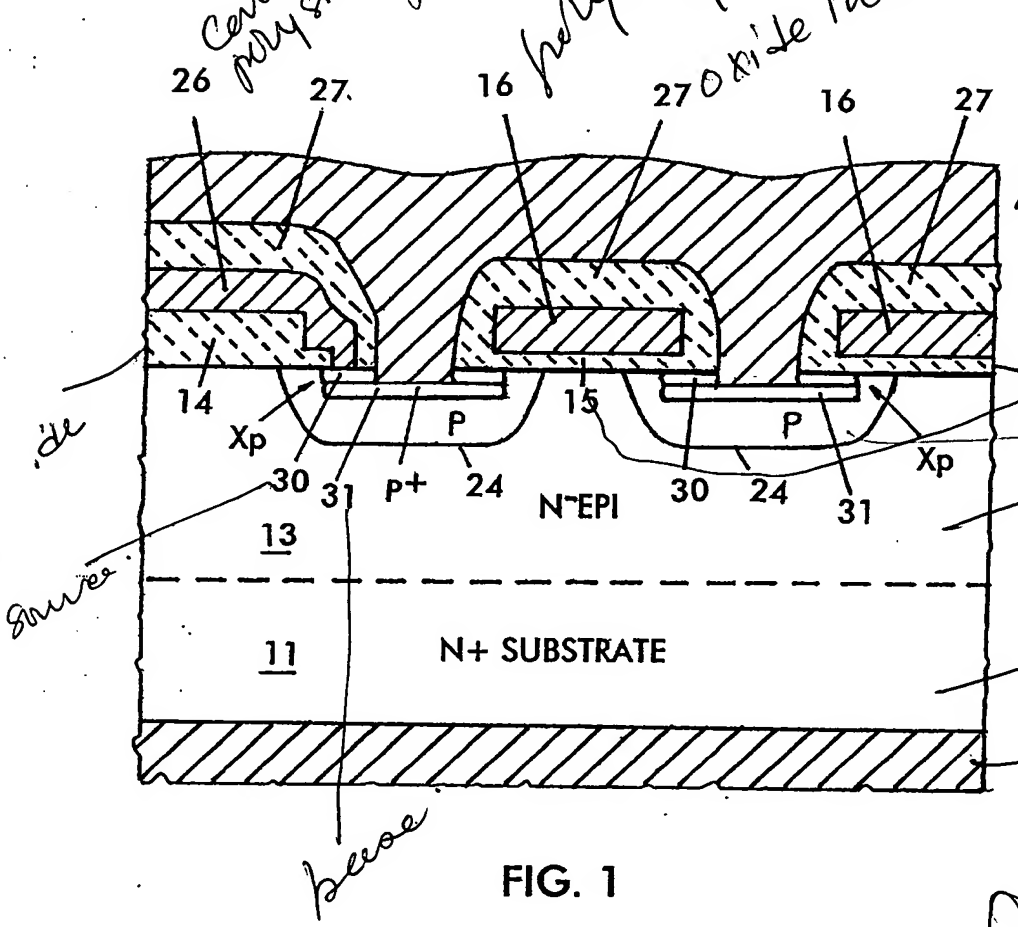
26
27
16
27
16
27
10
14
15
15
Xp
P
P
Xp
30
31
P+
24
N⁻EPI
30
24
31
13
11
N+ SUBSTRATE
12

FIG. 1

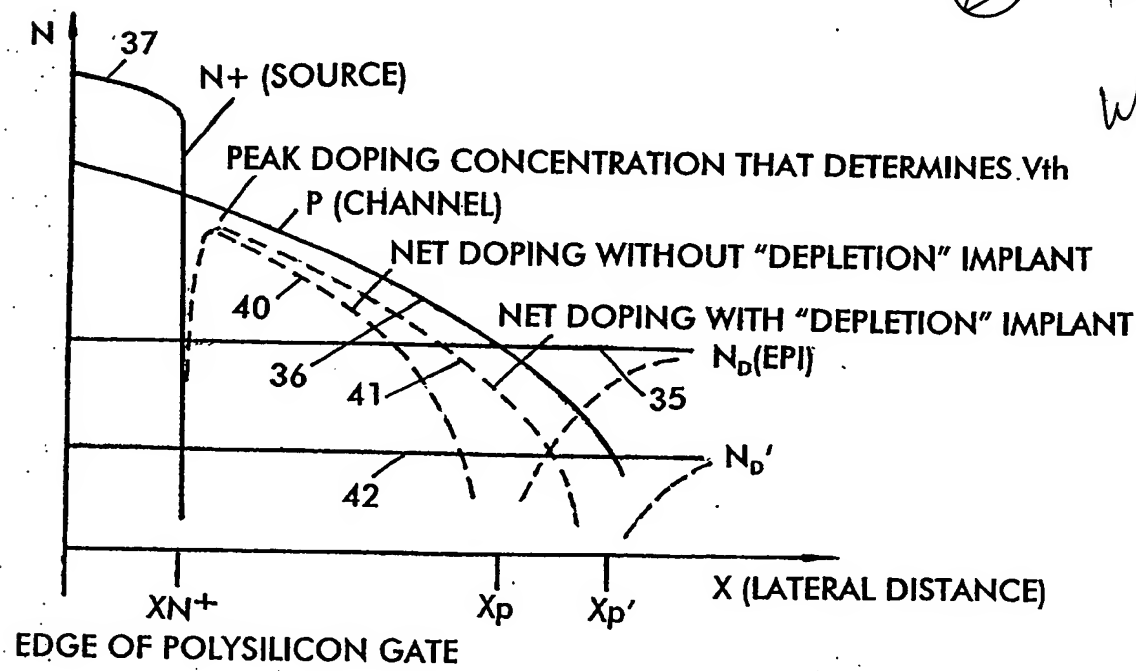
N
37
N+ (SOURCE)
PEAK DOPING CONCENTRATION THAT DETERMINES Vth
P (CHANNEL)
NET DOPING WITHOUT "DEPLETION" IMPLANT
40
NET DOPING WITH "DEPLETION" IMPLANT
N_D(EPI)
36
41
35
N_D'
42
XN+
Xp
Xp'
X (LATERAL DISTANCE)
EDGE OF POLYSILICON GATE

FIG. 2